

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL JUNCTION TYPE

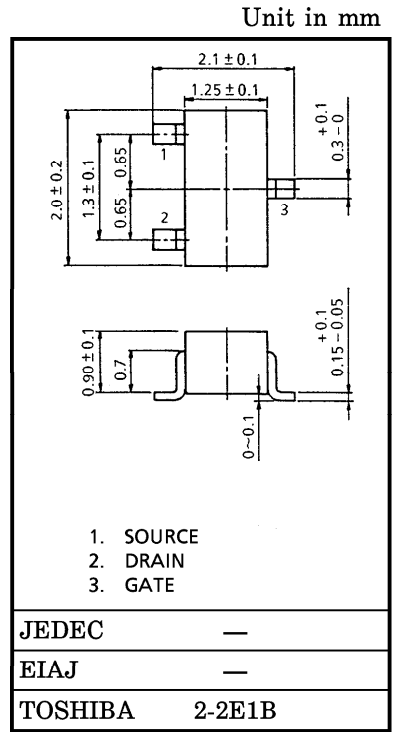
# 2SK1875

HIGH FREQUENCY AMPLIFIER APPLICATIONS  
 AM HIGH FREQUENCY AMPLIFIER APPLICATIONS  
 AUDIO FREQUENCY AMPLIFIER APPLICATIONS

- High  $|Y_{fs}|$  :  $|Y_{fs}|=25\text{mS (Typ.)}$
- Low  $C_{iss}$  :  $C_{iss}=7.5\text{pF (Typ.)}$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	$V_{GDS}$	-20	V
Gate Current	$I_G$	10	mA
Drain Power Dissipation	$P_D$	100	mW
Junction Temperature	$T_j$	125	°C
Storage Temperature Range	$T_{stg}$	-55~125	°C



Weight : 0.006 g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

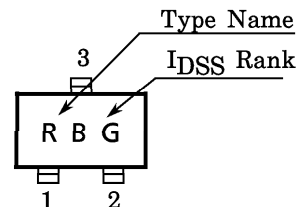
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	$I_{GSS}$	$V_{GS} = -15V, V_{DS} = 0V$	—	—	-1.0	nA
Gate-Drain Breakdown Voltage	$V(BR)_{GDS}$	$V_{DS} = 0V, I_G = -100\mu A$	-20	—	—	V
Drain Current	$I_{DSS}$ (Note)	$V_{DS} = 5V, V_{GS} = 0V$	6	—	32	mA
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$	$V_{DS} = 5V, I_D = 1\mu A$	—	—	-2.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 5V, V_{GS} = 0V, f = 1\text{kHz}$	15	25	—	mS
Input Capacitance	$C_{iss}$	$V_{DS} = 5V, V_{GS} = 0V, f = 1\text{MHz}$	—	7.5	10	pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DG} = 5V, I_D = 0V, f = 1\text{MHz}$	—	2	3	pF

Note :  $I_{DSS}$  Classification

GR : 6~12mA, BL : 10~20mA, V : 16~32mA  
 (G) (L) (V)

( )... $I_{DSS}$  Rank Marking

Marking



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